

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S48	4267	(low near3 dielectric) with (void trench hole via groove recess damascene opening)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/25 18:04
S49	0	S48 and (photoresist) near5 (low near3 dielectric void trench hole via groove recess damascene opening)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/25 18:05
S50	1153	S48 and (photoresist\$3 photo adj resist\$3) near5 (low near3 dielectric void trench hole via groove recess damascene opening)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/25 18:06
S51	164	S50 and (residue contaminant debris) with (low near3 dielectric void trench hole via groove recess damascene opening)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/25 18:08
S52	127	S51 and (residue contaminant debris) with (clean\$3 stip\$4 remov\$3)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/25 18:10
S53	120	S52 and (photoresist\$3 photo adj resist\$3) with (clean\$3 stip\$4 remov\$3)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/25 18:09
S54	99	S53 and (photoresist\$3 photo adj resist\$3 clean\$3 stip\$4 remov\$3) with plasma	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/25 18:12
S55	92	S54 and (residue contaminant debris) with (etch\$4)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/25 18:11
S56	12	S54 and (residue contaminant debris) with (etch\$4 near3 (wet dry))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/25 18:11
S57	56	S53 and (photoresist\$3 photo adj resist\$3 clean\$3 stip\$4 remov\$3) with (plasma with (hydrogen "h.sub.2"))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/25 18:13